

The RF MOSFET Line

Power Field Effect Transistor

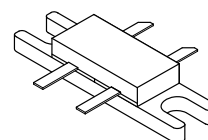
N-Channel Enhancement-Mode MOSFET

Designed primarily for wideband large-signal output and driver stages to 500 MHz.

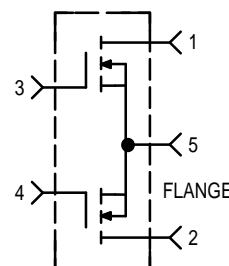
- Push-Pull Configuration Reduces Even Numbered Harmonics
- Typical Performance at 400 MHz, 28 Vdc
 - Output Power = 40 Watts
 - Gain = 13 dB
 - Efficiency = 50%
- Typical Performance at 175 MHz, 28 Vdc
 - Output Power = 40 Watts
 - Gain = 17 dB
 - Efficiency = 60%
- Excellent Thermal Stability, Ideally Suited for Class A Operation
- Facilitates Manual Gain Control, ALC and Modulation Techniques
- 100% Tested for Load Mismatch at All Phase Angles with 30:1 VSWR
- Low C_{RSS} — 4.5 pF @ $V_{DS} = 28$ Volts
- Circuit board photomaster available upon request by contacting RF Tactical Marketing in Phoenix, AZ.

MRF166W

**40 W, 500 MHz
TMOS BROADBAND
RF POWER FET**



CASE 412-01, Style 1



MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-Gate Voltage	V _{DSS}	65	Vdc
Drain-Gate Voltage (R _{GS} = 1.0 MΩ)	V _{DGR}	65	Vdc
Gate-Source Voltage	V _{GS}	± 40	Adc
Drain Current — Continuous	I _D	8.0	ADC
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	175 1.0	Watts °C/W
Storage Temperature Range	T _{stg}	-65 to +150	°C
Operating Junction Temperature	T _J	200	°C

THERMAL CHARACTERISTICS

Thermal Resistance — Junction to Case	R _{θJC}	1.0	°C/W
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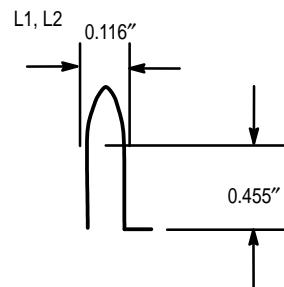
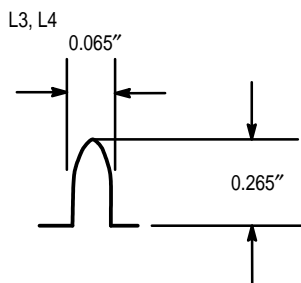
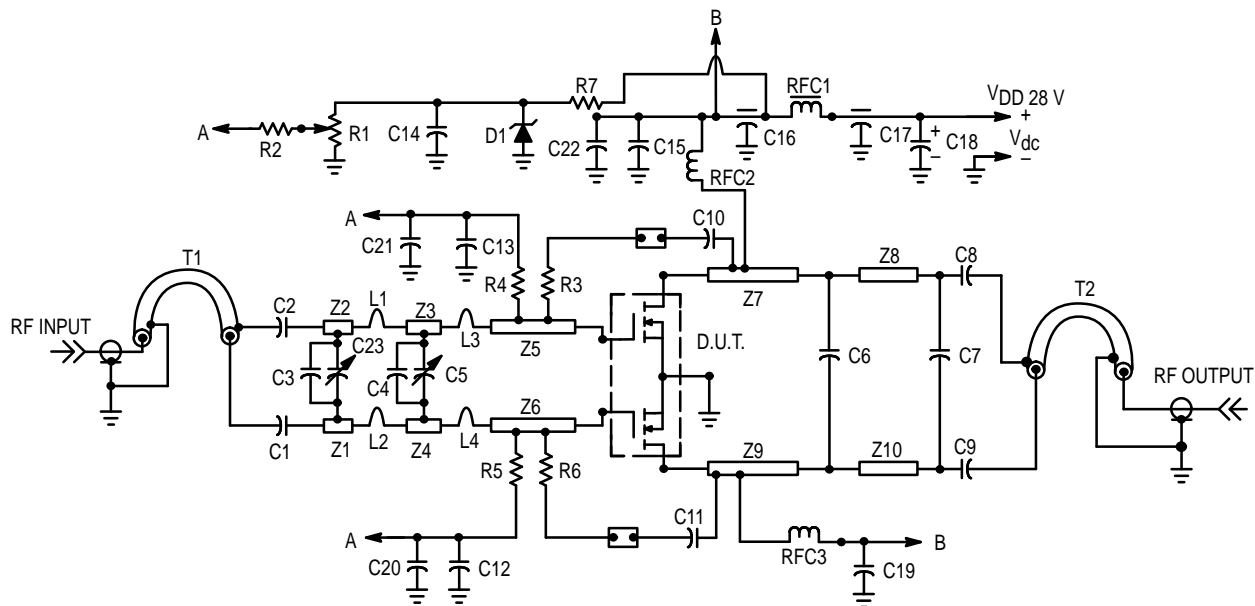
NOTE: Handling and Packaging — MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS (1)					
Drain–Source Breakdown Voltage ($V_{GS} = 0\text{ Vdc}$, $I_D = 5.0\text{ mA}$)	$V_{(BR)DSS}$	65	—	—	Vdc
Zero Gate Voltage Drain Current ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	1.0	mA
Gate–Source Leakage Current ($V_{GS} = 40\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1.0	μA
ON CHARACTERISTICS (1)					
Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 25\text{ mA}$)	$V_{GS(th)}$	1.0	3.0	6.0	Vdc
Forward Transconductance ($V_{DS} = 10\text{ Vdc}$, $I_D = 1.5\text{ A}$)	g_{fs}	600	800	—	mS
DYNAMIC CHARACTERISTICS (1)					
Input Capacitance ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$, $f = 1.0\text{ MHz}$)	C_{iss}	—	30	—	pF
Output Capacitance ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$, $f = 1.0\text{ MHz}$)	C_{oss}	—	35	—	pF
Reverse Transfer Capacitance ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$, $f = 1.0\text{ MHz}$)	C_{rss}	—	4.5	—	pF
FUNCTIONAL CHARACTERISTICS (2)					
Common Source Power Gain ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 40\text{ W}$, $f = 400\text{ MHz}$, $I_{DG} = 100\text{ mA}$)	G_{ps}	11	13	—	dB
Drain Efficiency ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 40\text{ W}$, $f = 400\text{ MHz}$, $I_{DG} = 100\text{ mA}$)	η	45	50	—	%
Electrical Ruggedness ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 40\text{ W}$, $f = 400\text{ MHz}$, $I_{DG} = 100\text{ mA}$) Load VSWR = 30:1, All phase angles at frequency of test	Ψ	No Degradation in Output Power			

(1) Each transistor chip measured separately.

(2) Both transistor chips operating in a push–pull amplifier.



C1, C2, C8, C9, C12, C13, C15	270 pF, Chip Cap	RFC1	Ferroxcube VK-200-19/4B
C3	5.6 pF, Chip Cap	RFC2, RFC3	10T, ID = 1/4", 18 AWG
C4	20 pF, Chip Cap	R1	10 kΩ, 10T
C5	0 - 20 pF, Johanson*	R2	9.2 kΩ, 1/2 W
C6	8.2 pF, Chip Cap	R3, R6	330 Ω, 1.0 W
C7	15 pF, Chip Cap	R4 R5	520 Ω, 1/4 W
C10, C11, C14, C19, C20, C21, C22	0.01 μF	R7	1.5 kΩ, 1/2 W
C16, C17	680 pF, Feedthru	T1, T2	Balun 2.0", 50 Ω Semi-Rigid Coax
C18	10 μF, 50 V	Z1, Z2	0.120 x 0.467"
C23	0 - 10 pF, Johanson*	Z3, Z4	0.120 x 0.55" *
D1	IN5343 - Motorola Zener	Z5, Z6	0.120 x 0.49"
L1, L2	Hair Pin Inductor #18 AWG, 0.065 W x 0.265 H	Z7, Z9	0.120 x 0.85"
L3, L4	Hair Pin Inductor #18 AWG, 0.116 W x 0.445 H	Z8, Z10	0.120 x 0.6" for C6

* C4, C5 Center of Z3 and Z4

Board Material - Teflon® Fiberglass
Dielectric Thickness = 0.030", ε_r = 2.55 Copper Clad, 2.0 oz. Copper

Figure 1. MRF166 400 MHz Test Circuit Schematic

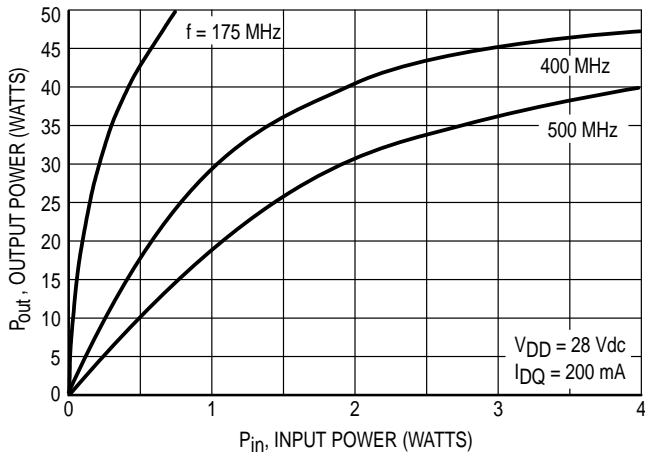


Figure 2. Output Power versus Input Power

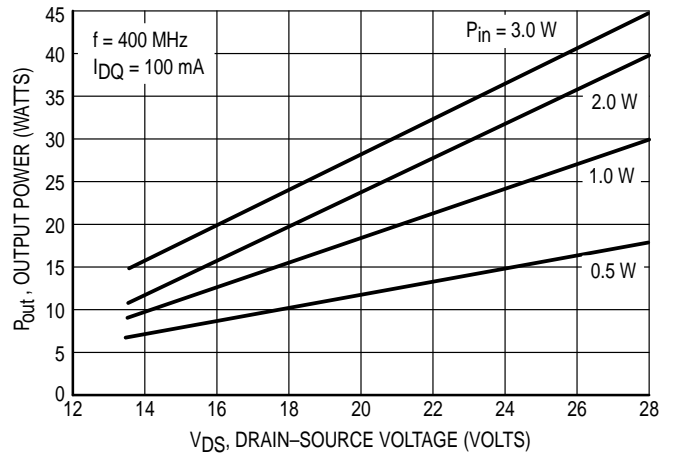


Figure 3. Output Power versus Voltage

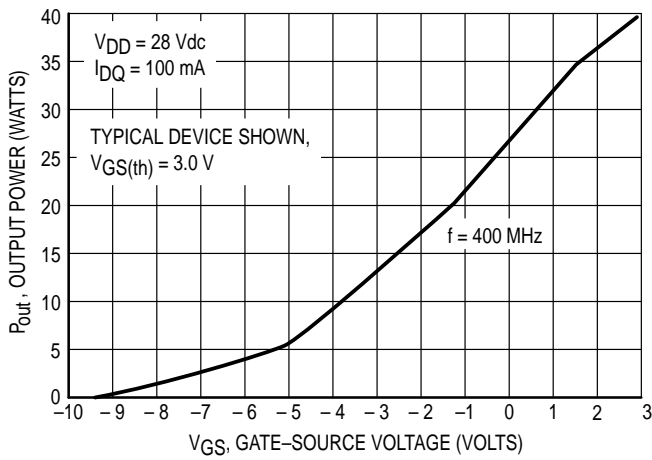


Figure 4. Output Power versus Gate Voltage

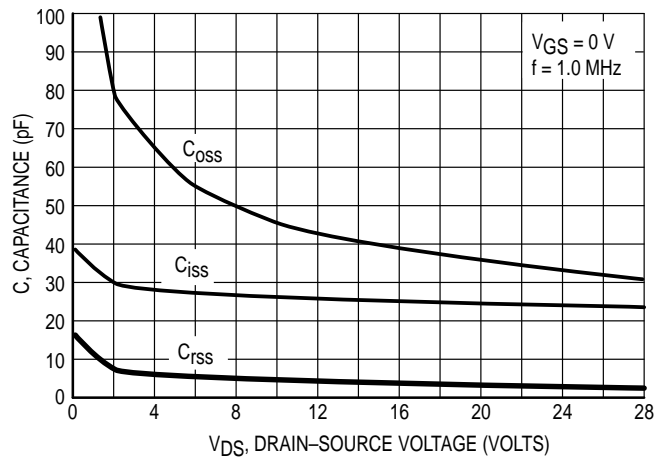
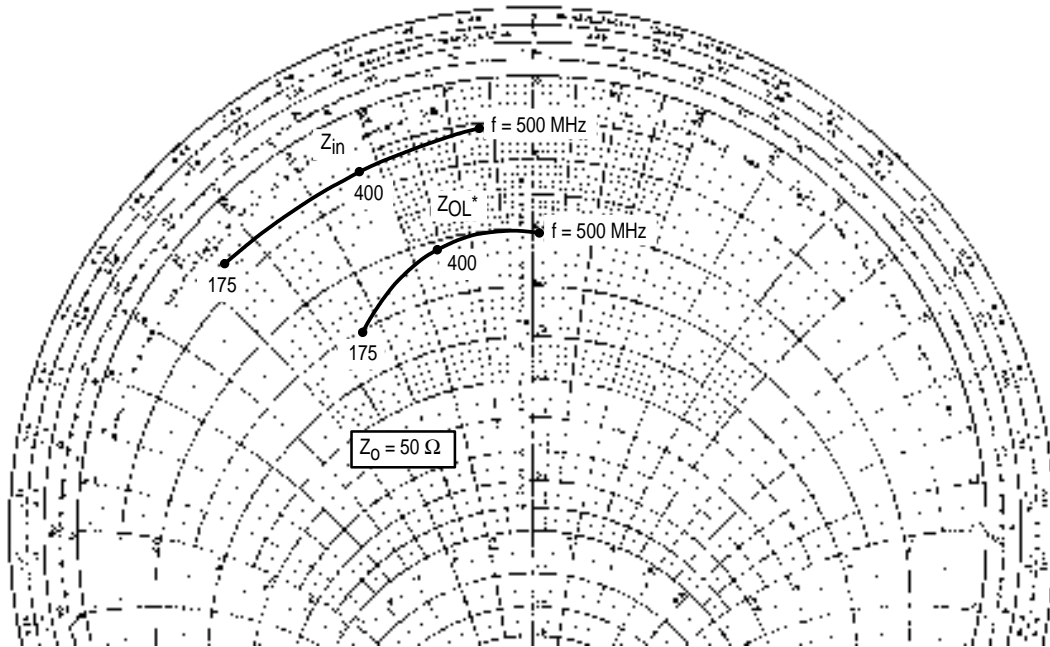


Figure 5. Capacitance versus Voltage



$V_{DD} = 28 \text{ Vdc}$, $I_{DQ} = 100 \text{ mA}$, $P_{out} = 40 \text{ W}$

f MHz	Z_{in} Ohms	Z_{OL}^* Ohms
175	$3.7 - j 22.4$	$15.2 - j 16.6$
400	$3.6 - j 10.99$	$10.3 - j 7.99$
500	$2.6 - j 3.2$	$10.2 + j 0.5$

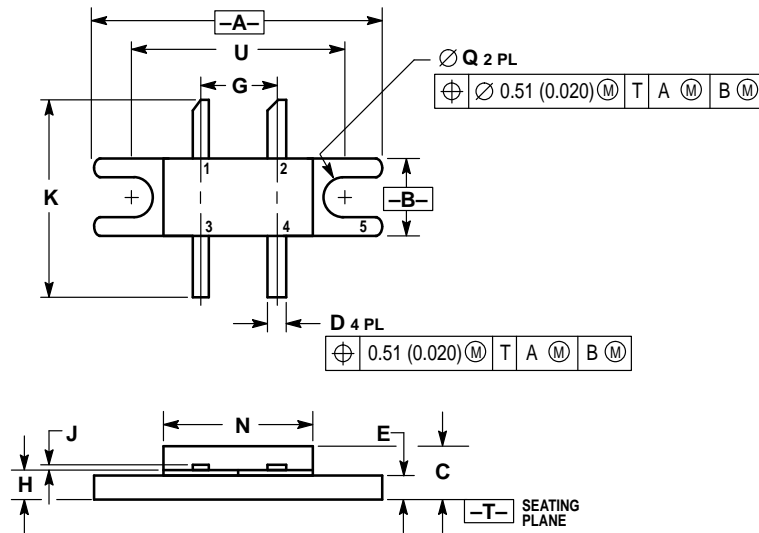
Table 1. Input and Output Impedances

Z_{OL}^* = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage and frequency.

NOTE: Input and output impedance values given are measured from gate to gate and drain to drain respectively.

Figure 6. Series Equivalent Input/Output Impedance

PACKAGE DIMENSIONS



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.965	0.985	24.52	25.01
B	0.245	0.265	6.23	6.73
C	0.165	0.185	4.20	4.69
D	0.050	0.070	1.27	1.77
E	0.070	0.080	1.78	2.03
G	0.254 BSC		6.45 BSC	
H	0.095	0.105	2.42	2.66
J	0.003	0.006	0.08	0.15
K	0.625	0.675	15.88	17.14
N	0.495	0.520	12.58	13.20
Q	0.120	0.140	3.05	3.55
U	0.725 BSC		18.42 BSC	

- STYLE 1:
1. DRAIN
 2. DRAIN
 3. GATE
 4. GATE
 5. SOURCE

**CASE 412-01
ISSUE O**

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MRF166W/D

